

**Notice of References Cited**Application/Control No.  
10/063,128Applicant(s)/Patent Under  
Reexamination  
LIANG ET AL.Examiner  
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2814

Page 1 of 1

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.